November 2011

# FDME410NZT

# N-Channel PowerTrench® MOSFET 20 V, 7 A, 26 m $\Omega$

### **Features**

- Max  $r_{DS(on)}$  = 26 m $\Omega$  at  $V_{GS}$  = 4.5 V,  $I_D$  = 7 A
- Max  $r_{DS(on)}$  = 31 m $\Omega$  at  $V_{GS}$  = 2.5 V,  $I_D$  = 6 A
- Max  $r_{DS(on)} = 39 \text{ m}\Omega$  at  $V_{GS} = 1.8 \text{ V}$ ,  $I_D = 5 \text{ A}$
- Max  $r_{DS(on)}$  = 53 m $\Omega$  at  $V_{GS}$  = 1.5 V,  $I_D$  = 4 A
- Low profile: 0.55 mm maximum in the new package MicroFET 1.6x1.6 **Thin**
- Free from halogenated compounds and antimony oxides
- HBM ESD protection level > 1800V (Note3)
- RoHS Compliant

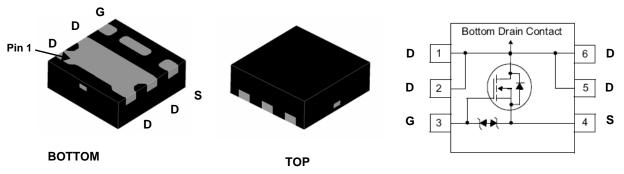


### **General Description**

This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the  $r_{DS(ON)}$  @ VGS = 1.5 V on special MicroFET leadframe.

## **Applications**

- Li-Ion Battery Pack
- Baseband Switch
- Load Switch
- DC-DC Conversion



MicroFET 1.6x1.6 Thin

# **MOSFET Maximum Ratings** $T_A = 25 \ \mathfrak{C}$ unless otherwise noted

Symbol	Paramet		Ratings	Units	
V <sub>DS</sub>	Drain to Source Voltage	Drain to Source Voltage			
$V_{GS}$	Gate to Source Voltage			±8	V
	Drain Current -Continuous	T <sub>A</sub> = 25 ℃	(Note 1a)	7	۸
'D	-Pulsed			15	_ A
D	Power Dissipation for Single Operation	T <sub>A</sub> = 25 ℃	(Note 1a)	2.1	W
$P_{D}$	Power Dissipation for Single Operation	T <sub>A</sub> = 25 ℃	(Note 1b)	0.7	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range			-55 to +150	C

### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	60	€/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	175	C/VV

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
6T	FDME410NZT	MicroFET 1.6x1.6 <b>Thin</b>	7 "	8 mm	5000 units

# Electrical Characteristics T<sub>J</sub> = 25 ℃ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
$BV_DSS$	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, referenced to 25 °C		18		mV/℃
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V			1	μΑ
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$			±10	μΑ

### On Characteristics

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	0.4	0.7	1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = 250 μA, referenced to 25 °C		-3		mV/℃
	$V_{GS} = 4.5 \text{ V}, I_D = 7 \text{ A}$		19	26		
		$V_{GS} = 2.5 \text{ V}, I_D = 6 \text{ A}$		20	31	
r <sub>DS(on)</sub> Drain to Source On Resistance	Drain to Source On Resistance	$V_{GS} = 1.8 \text{ V}, I_D = 5 \text{ A}$		24	39	mΩ
	Drain to Source On Resistance	$V_{GS} = 1.5 \text{ V}, I_D = 4 \text{ A}$		31	53	11152
	$V_{GS} = 4.5 \text{ V}, I_D = 7 \text{ A},$ $T_J = 125 \text{ C}$		24	36		
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 7 \text{ A}$		35		S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 40.V V 0.V	770	1025	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	115	155	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1/11/12	75	115	pF
$R_g$	Gate Resistance		1.9		Ω

### **Switching Characteristics**

	J				
t <sub>d(on)</sub>	Turn-On Delay Time		7.3	15	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 10 \text{ V}, I_{D} = 7 \text{ A}$ $V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$	3.4	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 4.5 V, K <sub>GEN</sub> = 6.22	27	43	ns
t <sub>f</sub>	Fall Time		3.2	10	ns
$Q_g$	Total Gate Charge	V 40 V 1 7 A	9.2	13	nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DD} = 10 \text{ V}, I_{D} = 7 \text{ A}$ $V_{GS} = 4.5 \text{ V}$	1.1		nC
$Q_{gd}$	Gate to Drain "Miller" Charge	vGS - 4.5 v	1.6		nC

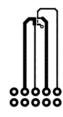
### **Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.6 A (Note 2)		0.7	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	L _ 7 A di/dt _ 100 A/us		15	27	ns
Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> = 7 A, di/dt = 100 A/μs		3.5	10	nC

<sup>1.</sup> R<sub>0,1A</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0,1C</sub> is guaranteed by design while R<sub>0,1C</sub> is determined by the user's board design.



a. 60 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.



b. 175 °C/W when mounted on  $\,a\,$ minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty cycle < 2.0%.
- 3. The diode connected between the gate and source serves only as protection ESD. No gate overvoltage rating is implied.

### Typical Characteristics T<sub>J</sub> = 25 ℃ unless otherwise noted

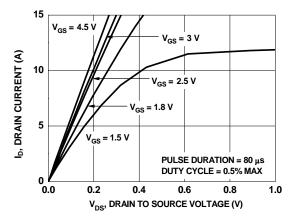


Figure 1. On-Region Characteristics

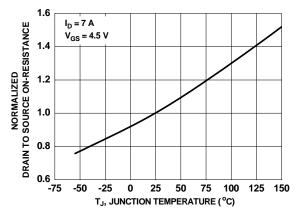


Figure 3. Normalized On-Resistance vs Junction Temperature

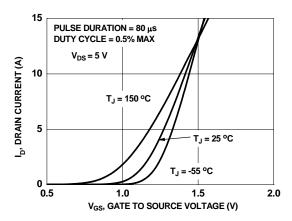


Figure 5. Transfer Characteristics

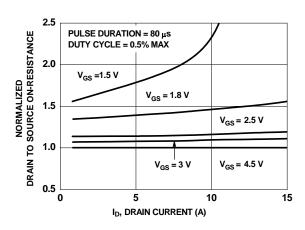


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

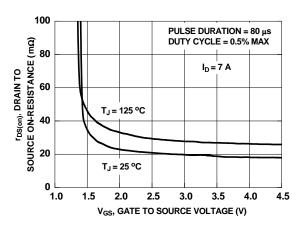


Figure 4. On-Resistance vs Gate to Source Voltage

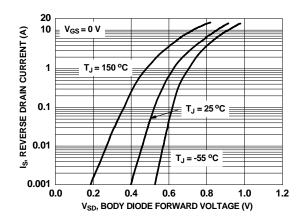


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics T<sub>J</sub> = 25 ℃ unless otherwise noted

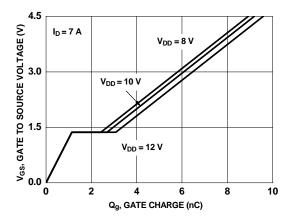


Figure 7. Gate Charge Characteristics

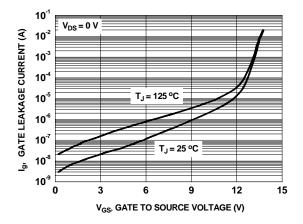


Figure 9. Gate Leakage Current vs Gate to Source Voltage

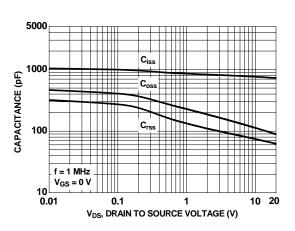


Figure 8. Capacitance vs Drain to Source Voltage

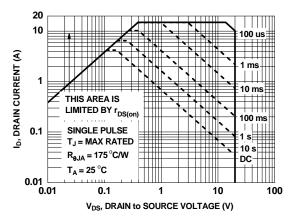


Figure 10. Forward Bias Safe Operating Area

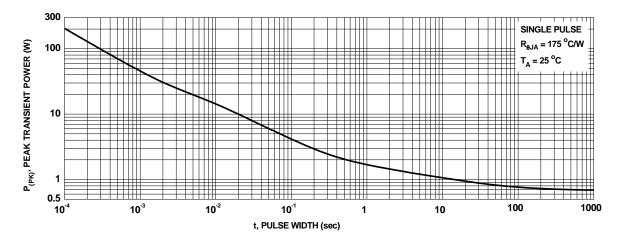


Figure 11. Single Pulse Maximum Power Dissipation

# Typical Characteristics T<sub>J</sub> = 25 ℃ unless otherwise noted

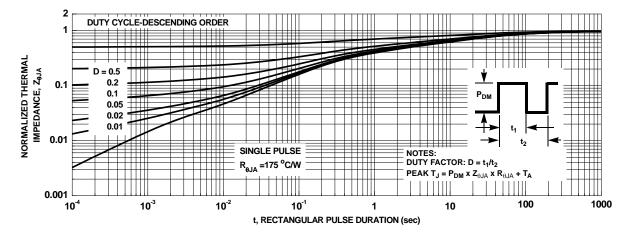
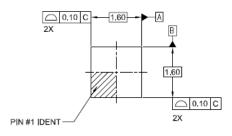
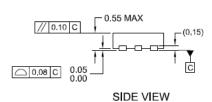


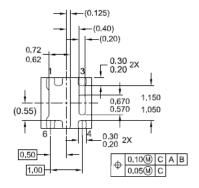
Figure 12. Junction-to-Ambient Transient Thermal Response Curve

# **Dimensional Outline and Pad Layout**

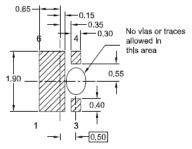


TOP VIEW

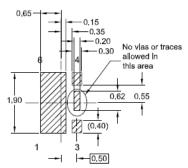




**BOTTOM VIEW** 



RECOMMENDED LAND PATTERN OPT 1



RECOMMENDED LAND PATTERN OPT 2

### NOTES:

- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY





The Power Franchise®

wer

franchise TinyBoost™

TinyBuck™

TinyCalc™

TinyLogic<sup>®</sup>
TINYOPTO™

TinyPower™ TinyPWM™

TriFault Detect™

TRUECURRENT®\*

TinyWire™

μSerDes™

Ultra FRFET™

UniFET™

VisualMax™

VoltagePlus™

**VCXTM** 

XSTM

**UHC®** 

TranSiC<sup>®</sup>

### **TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™ AccuPower™ Auto-SPM™ AX-CAP™ BitSiC<sup>®</sup>

Build it Now™ CorePLUS™ CorePOWER™ CROSSVOLT<sup>TM</sup>

Current Transfer Logic™ DEUXPEED®

Dual Cool™ EcoSPARK<sup>®</sup> EfficentMax™ ESBC™

 $\mathsf{Fairchild}^{\mathbb{R}}$ 

Fairchild Semiconductor® FACT Quiet Series™ FACT<sup>®</sup>

FAST® FastvCore™ FETBench™ FlashWriter® \* FPS™ F-PFS™ FRFET®

Global Power Resource<sup>SM</sup> Green FPS™

Green FPS™ e-Series™ Gmax™ GTO™ IntelliMAX™

ISOPLANAR™ Marking Small Speakers Sound Louder

and Better™ MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™

MicroPak2™ MillerDrive™ MotionMax™ Motion-SPM™ mWSaver™ OptoHiT™ OPTOLOGIC® OPTOPLANAR®

Sync-Lock™

PowerTrench® PowerXS™

Programmable Active Droop™

 $QS^{TM}$ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™ SPM<sup>®</sup>

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS<sup>®</sup> SyncFET™

SYSTEM ®\* GENERAL

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or

### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, falled application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

### PRODUCT STATUS DEFINITIONS **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information Formative / In Design		Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 160